



# TFF1024HN

## Integrated mixer oscillator PLL for satellite LNB

Rev. 1 — 13 January 2015

Product data sheet

## 1. General description

The TFF1024HN is an integrated downconverter for use in Low Noise Block (LNB) converters in a 10.70 GHz to 12.85 GHz  $K_u$  band satellite receiver system.

## 2. Features and benefits

- Low current consumption integrated pre-amplifier, mixer, buffer amplifier and PLL synthesizer
- Flat gain over frequency
- Single 5 V supply pin
- Low cost 25 MHz crystal
- Crystal controlled LO frequency generation
- Switched LO frequency (selectable to 9.75 GHz, 10.00 GHz, 10.25 GHz, 10.55 GHz, 10.60 GHz, 10.75 GHz, 11.25 GHz or 11.30 GHz) with a 25 MHz crystal as reference
- Other LO frequencies within the 9.75 GHz to 11.30 GHz range can be realized by using an alternative reference frequency
- Low phase noise
- Low spurious
- Low external component count
- Alignment-free concept
- ESD protection on all pins

## 3. Applications

- $K_u$  band LNB converters for VSAT and digital satellite reception (DVB-S / DVB-S2)

## 4. Quick reference data

**Table 1. Quick reference data**

$9.75 \text{ GHz} \leq f_{LO} \leq 11.30 \text{ GHz}$ ; operating conditions of [Table 6](#) apply.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CC}$	supply voltage	RF input and IF output AC coupled	[1] 4.5	5	5.5	V
$I_{CC}$	supply current	RF input and IF output AC coupled	[1] -	56	70	mA
$NF_{SSB}$	single sideband noise figure	$f_{IF} = 1450 \text{ MHz}$ ; $T_{amb} = 25 \text{ }^\circ\text{C}$ ; $10.55 \text{ GHz} \leq f_{LO} \leq 10.60 \text{ GHz}$	-	9.0	11.0	dB
$f_{RF}$	RF frequency		[2] 10.70	-	12.85	GHz



**Table 1. Quick reference data ...continued**  
 9.75 GHz ≤ f<sub>LO</sub> ≤ 11.30 GHz; operating conditions of [Table 6](#) apply.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G <sub>conv</sub>	conversion gain	f <sub>IF</sub> = 1450 MHz				
		f <sub>LO</sub> = 10.55 GHz	29.8	34.3	38.8	dB
		f <sub>LO</sub> = 10.60 GHz	29.8	34.3	38.8	dB
S <sub>11</sub>	input reflection coefficient	10.70 GHz ≤ f <sub>RF</sub> ≤ 12.85 GHz	-	-10	-	dB
S <sub>22</sub>	output reflection coefficient	950 MHz ≤ f <sub>IF</sub> ≤ 2150 MHz; Z <sub>0</sub> = 75 Ω	-	-10	-	dB
IP <sub>3o</sub>	output third-order intercept point	carrier power = -10 dBm (measured at output)				
		f <sub>IF</sub> = 1450 MHz; 9.75 GHz ≤ f <sub>LO</sub> ≤ 10.75 GHz	14	18	-	dBm
		f <sub>IF</sub> = 1250 MHz; 11.25 GHz ≤ f <sub>LO</sub> ≤ 11.30 GHz	14	18	-	dBm

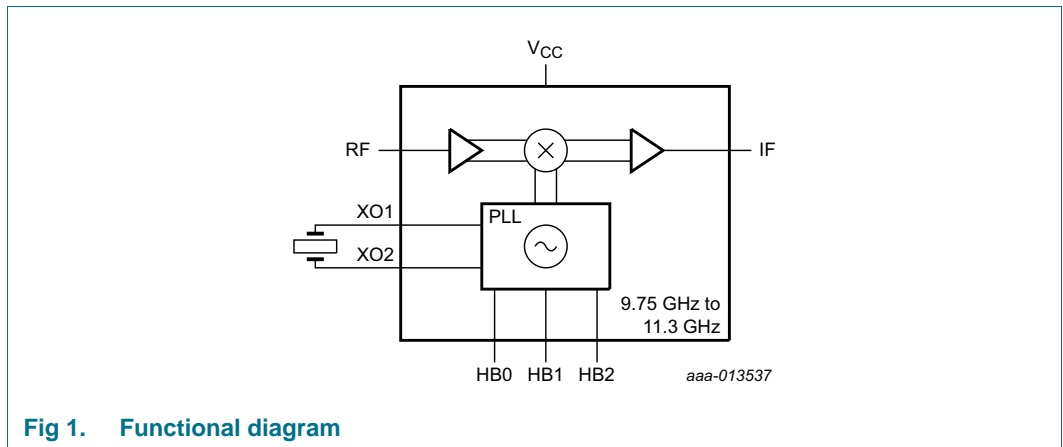
- [1] DC values.
- [2] See [Table 4](#) for specific values at certain settings of pins HB0, HB1 and HB2.

## 5. Ordering information

**Table 2. Ordering information**

Type number	Package		Version
	Name	Description	
TFF1024HN	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1

## 6. Functional diagram



## 7. Pinning information

### 7.1 Pinning

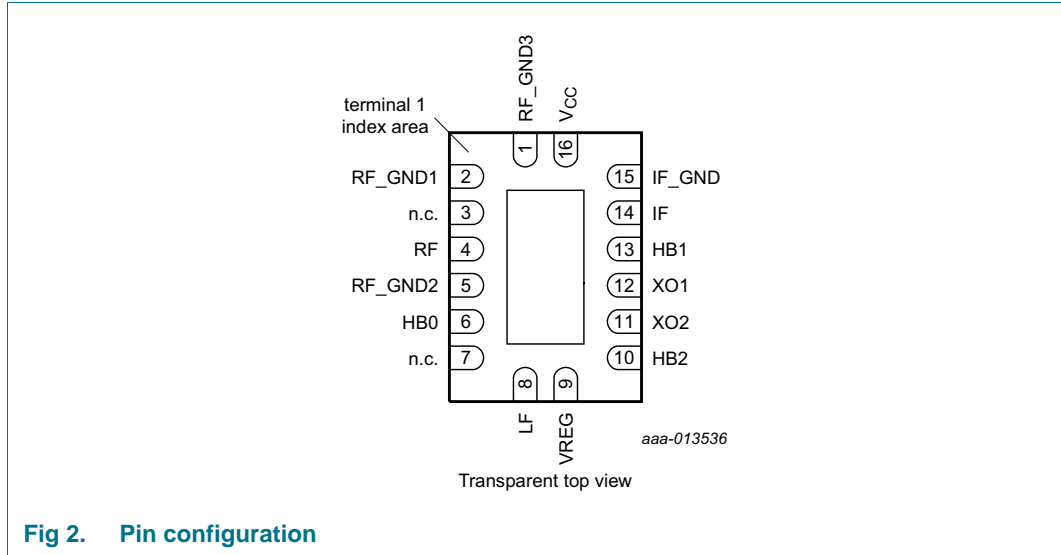


Fig 2. Pin configuration

### 7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
GND	0	ground (exposed die pad)
RF_GND3	1	RF ground. Connect this pin to the exposed die pad landing.
RF_GND1	2	RF ground. Connect this pin to the exposed die pad landing and the RF input CPW line.
n.c.	3	not connected. Connect to RF on PCB. [1]
RF	4	RF input.
RF_GND2	5	RF ground. Connect this pin to the exposed die pad landing and the RF input CPW line.
HB0	6	LO frequency selection, LSB. Connect this pin to GND for "0", leave open for "1". Also see Table 4.
n.c.	7	not connected. Use this pin to route the ground layer on top of the PCB to the exposed die pad.
LF	8	Loop filter PLL. Connect loop filter between this pin and VREG (pin 9).
VREG	9	Regulated output voltage for PLL loop filter. Connect loop filter to this pin. Decouple against die pad via pin 7.
HB2	10	LO frequency selection, MSB. Connect this pin to GND for "0", leave open for "1". Also see Table 4.
XO2	11	Crystal connection 2. Connect crystal between this pin and XO1 (pin 12).
XO1	12	Crystal connection 1. Connect crystal between this pin and XO2 (pin 11).
HB1	13	LO frequency selection. Connect this pin to GND for "0", leave open for "1". Also see Table 4.
IF	14	IF output
IF_GND	15	IF output ground. Connect this pin to the exposed die pad landing and the output transmission line ground.
V <sub>CC</sub>	16	Supply voltage

[1] The distance between the outer edges of pin 2 and pin 3 is 740 μm. This gives an optimum transition from a 1.1 mm wide, Z<sub>0</sub> = 50 Ω line to the TFF1024HN on a Rogers RO4223 Printed-Circuit Board (PCB) material of 0.5 mm height.

## 8. Functional description

### 8.1 LO frequency selection

**Table 4. LO frequency selection table**

See [Figure 1](#) for the functional diagram.

f <sub>LO</sub> (GHz)	f <sub>xtal</sub> (MHz)	HB2 (pin 10)	HB1 (pin 13)	HB0 (pin 6)	f <sub>RF</sub> (GHz)		f <sub>IF</sub> (MHz)	
					Min	Max	Min	Max
9.75	25	0	0	0	10.70	11.90	950	2150
10.00	25	0	0	1	10.95	12.15	950	2150
10.25	25	0	1	0	11.20	12.40	950	2150
10.45 <sup>[1]</sup>	24.76	0	1	1	11.40	12.60	950	2150
10.55	25	0	1	1	11.50	12.70	950	2150
10.60	25	1	0	0	11.55	12.75	950	2150
10.75	25	1	0	1	11.70	12.85	950	2100
11.25	25	1	1	0	12.20	12.85	950	1600
11.30	25	1	1	1	12.25	12.85	950	1550

[1] For frequencies that cannot be achieved using the 25 MHz crystal choose the closest frequency and adapt the crystal frequency.

Example: 10.45 GHz. This can be achieved by choosing 10.55 GHz. The divider ratio is 422. 10.45 GHz will be achieved with a crystal frequency of  $10.45 \text{ GHz} / 422 = 24.76303 \text{ MHz}$ .

## 9. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+6	V
V <sub>i</sub>	input voltage	on pin HB0	-0.5	+6	V
		on pin HB1	-0.5	+6	V
		on pin HB2	-0.5	+6	V
T <sub>stg</sub>	storage temperature		-40	+125	°C

## 10. Recommended operating conditions

**Table 6. Operating conditions**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>CC</sub>	supply voltage	RF input and IF output AC coupled <sup>[1]</sup>	4.5	5	5.5	V
V <sub>i</sub>	input voltage	on pin HB0	0	-	2.7	V
		on pin HB1	0	-	2.7	V
		on pin HB2	0	-	2.7	V
I <sub>CC(startup)</sub>	start-up supply current	during 30 ms only at supply power-on	300	-	-	mA
T <sub>amb</sub>	ambient temperature		-40	+25	+85	°C
Z <sub>0</sub>	characteristic impedance		-	50	-	Ω
f <sub>RF</sub>	RF frequency		<sup>[2]</sup> 10.70	-	12.85	GHz

Table 6. Operating conditions ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
f <sub>LO</sub>	LO frequency	HB2 = 0; HB1 = 0; HB0 = 0	[3]	-	9.75	-	GHz
		HB2 = 1; HB1 = 1; HB0 = 1	[4]	-	11.30	-	GHz
f <sub>IF</sub>	IF frequency		[2]	950	-	2150	MHz
C <sub>L(xtal)</sub>	crystal load capacitance		-	10	-	pF	
ESR	equivalent series resistance		-	-	40	Ω	
f <sub>xtal</sub>	crystal frequency		-	25	-	MHz	

- [1] DC values.
- [2] See Table 4 for specific values at certain settings of pins HB0, HB1 and HB2.
- [3] The minimum LO frequency is specified. See Table 4 for other specific values at certain settings of pins HB0, HB1 and HB2.
- [4] The maximum LO frequency is specified. See Table 4 for other specific values at certain settings of pins HB0, HB1 and HB2.

## 11. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case		35	K/W

## 12. Characteristics

Table 8. Characteristics

9.75 GHz ≤ f<sub>LO</sub> ≤ 11.30 GHz; operating conditions of Table 6 apply.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
I <sub>CC</sub>	supply current	RF input and IF output AC coupled	[1]	-	56	70	mA
Φ <sub>nλ(itg)</sub> RMS	RMS integrated phase noise density	loop bandwidth = crossover bandwidth; low ESR crystal used (ESR < 20 Ω)					
		integration offset frequency = 1 kHz to 1 MHz	-	1.2	2.2	deg	
		integration offset frequency = 10 kHz to 13 MHz	-	1.2	2.2	deg	
NF <sub>SSB</sub>	single sideband noise figure	f <sub>IF</sub> = 1450 MHz; T <sub>amb</sub> = 25 °C					
		f <sub>LO</sub> = 9.75 GHz	-	8.8	10.8	dB	
		10.55 GHz ≤ f <sub>LO</sub> ≤ 10.60 GHz	-	9.0	11.0	dB	
		f <sub>IF</sub> = 1250 MHz; T <sub>amb</sub> = 25 °C					
G <sub>conv</sub>	conversion gain	11.25 GHz ≤ f <sub>LO</sub> ≤ 11.30 GHz	-	9.5	11.5	dB	
		f <sub>IF</sub> = 1450 MHz					
		f <sub>LO</sub> = 9.75 GHz	29.6	34.1	38.6	dB	
		f <sub>LO</sub> = 10.00 GHz	29.5	34.0	38.5	dB	
		f <sub>LO</sub> = 10.25 GHz	29.5	34.0	38.5	dB	
		f <sub>LO</sub> = 10.55 GHz	29.8	34.3	38.8	dB	
		f <sub>LO</sub> = 10.60 GHz	29.8	34.3	38.8	dB	
		f <sub>LO</sub> = 10.75 GHz	30.2	34.7	39.2	dB	
		f <sub>IF</sub> = 1250 MHz					
f <sub>LO</sub> = 11.25 GHz	30.2	34.7	39.2	dB			
f <sub>LO</sub> = 11.30 GHz	30.1	34.6	39.1	dB			

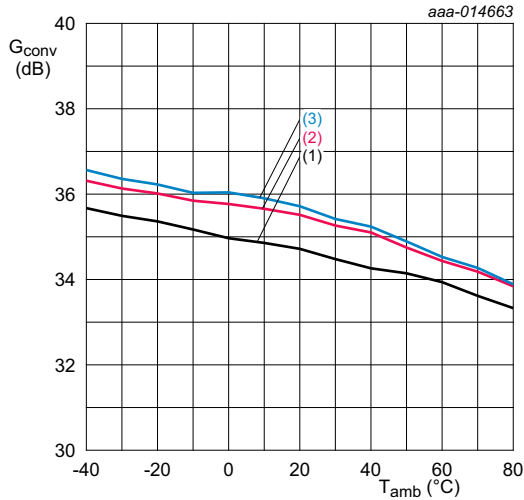
**Table 8. Characteristics ...continued**  
 $9.75 \text{ GHz} \leq f_{LO} \leq 11.30 \text{ GHz}$ ; operating conditions of [Table 6](#) apply.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$\Delta G_{conv}/\Delta f$	conversion gain variation with frequency	over IF band; $-40 \text{ }^\circ\text{C} \leq T_{amb} \leq +85 \text{ }^\circ\text{C}$ ; $V_{CC} = 5.0 \text{ V}$				
		$f_{LO} = 9.75 \text{ GHz}$ [2]	-	-	2.5	dB
		$f_{LO} = 10.00 \text{ GHz}$ [2]	-	-	3.0	dB
		$f_{LO} = 10.25 \text{ GHz}$ [2]	-	-	3.6	dB
		$f_{LO} = 10.55 \text{ GHz}$ [2]	-	-	4.0	dB
		$f_{LO} = 10.60 \text{ GHz}$ [2]	-	-	4.0	dB
		$f_{LO} = 10.75 \text{ GHz}$ [2]	-	-	4.0	dB
		$f_{LO} = 11.25 \text{ GHz}$ [2]	-	-	3.0	dB
		$f_{LO} = 11.30 \text{ GHz}$ [2]	-	-	3.0	dB
	in every 36 MHz band; $-40 \text{ }^\circ\text{C} \leq T_{amb} \leq +85 \text{ }^\circ\text{C}$ ; $V_{CC} = 5.0 \text{ V}$		-	-	0.6	dB
$S_{11}$	input reflection coefficient	$10.70 \text{ GHz} \leq f_{RF} \leq 12.85 \text{ GHz}$	-	-10	-	dB
$S_{22}$	output reflection coefficient	$950 \text{ MHz} \leq f_{IF} \leq 2150 \text{ MHz}$ ; $Z_0 = 75 \text{ } \Omega$	-	-10	-	dB
$IP_{3o}$	output third-order intercept point	carrier power is $-10 \text{ dBm}$ (measured at the output)				
		$f_{IF} = 1450 \text{ MHz}$ ; $9.75 \text{ GHz} \leq f_{LO} \leq 10.75 \text{ GHz}$	14	18	-	dBm
		$f_{IF} = 1250 \text{ MHz}$ ; $11.25 \text{ GHz} \leq f_{LO} \leq 11.30 \text{ GHz}$	14	18	-	dBm
$P_{L(1dB)}$	output power at 1 dB gain compression	measured at the output				
		$f_{IF} = 1450 \text{ MHz}$ ; $9.75 \text{ GHz} \leq f_{LO} \leq 10.75 \text{ GHz}$	2	6	-	dBm
		$f_{IF} = 1250 \text{ MHz}$ ; $11.25 \text{ GHz} \leq f_{LO} \leq 11.30 \text{ GHz}$	2	6	-	dBm
$\alpha_{L(RF)o}$	local oscillator RF leakage	$f_c = f_{LO}$ ; span = 100 MHz; RBW = 50 kHz; VBW = 200 kHz	-	-	-35	dBm
$V_{IL}$	LOW-level input voltage	on pin HB0	-	-	0.8	V
		on pin HB1	-	-	0.8	V
		on pin HB2	-	-	0.8	V
$V_{IH}$	HIGH-level input voltage	on pin HB0	1.6	-	2.7	V
		on pin HB1	1.6	-	2.7	V
		on pin HB2	1.6	-	2.7	V
$R_{pu}$	pull-up resistance	on pin HB0	80	110	140	k $\Omega$
		on pin HB1	80	110	140	k $\Omega$
		on pin HB2	80	110	140	k $\Omega$

[1] DC values.

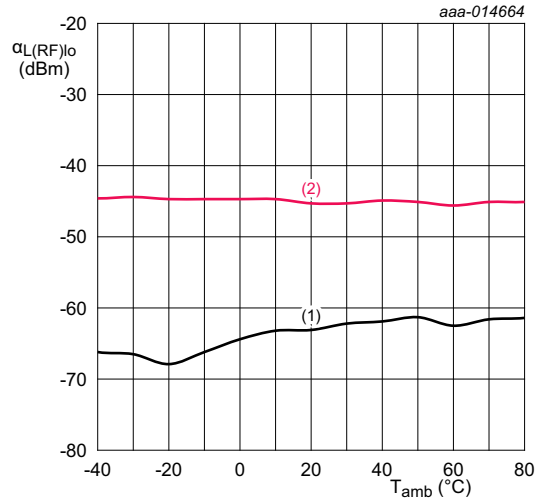
[2] See [Table 4](#) for the corresponding  $f_{IF}$  ranges.

12.1 Graphs



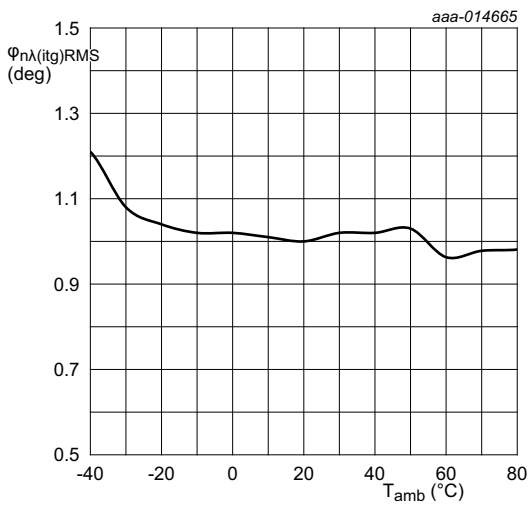
$V_{CC} = 5\text{ V}; f_{IF} = 1550\text{ MHz}.$   
 (1)  $f_{LO} = 9.75\text{ GHz}$   
 (2)  $f_{LO} = 10.60\text{ GHz}$   
 (3)  $f_{LO} = 11.30\text{ GHz}$

**Fig 3. Conversion gain as a function of ambient temperature; typical values**



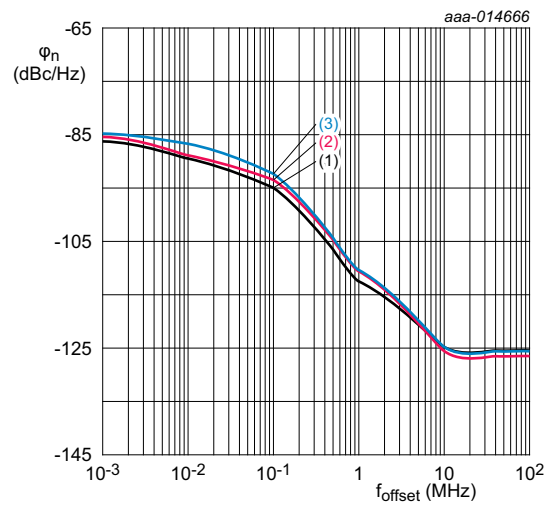
$V_{CC} = 5\text{ V}.$   
 (1)  $f_{LO} = 9.75\text{ GHz}$   
 (2)  $f_{LO} = 11.30\text{ GHz}$

**Fig 4. Local oscillator RF leakage as a function of ambient temperature; typical values**



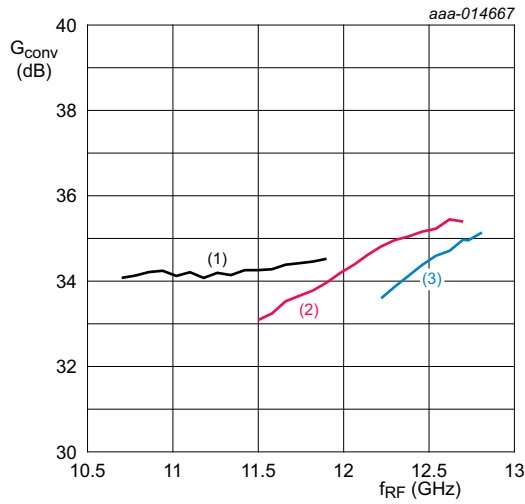
$V_{CC} = 5\text{ V}; f_{LO} = 10.55\text{ GHz}.$

**Fig 5. RMS integrated phase noise density as a function of ambient temperature; typical values**



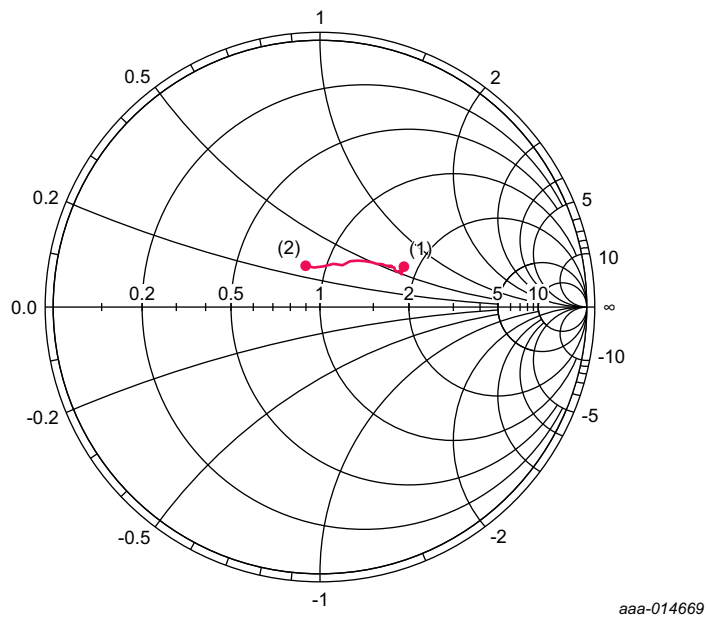
$V_{CC} = 5\text{ V}; T_{amb} = 25\text{ °C}.$   
 (1)  $f_{LO} = 9.75\text{ GHz}$   
 (2)  $f_{LO} = 10.60\text{ GHz}$   
 (3)  $f_{LO} = 11.30\text{ GHz}$

**Fig 6. Phase noise as a function of offset frequency; typical values**



- V<sub>CC</sub> = 5 V.
- (1) f<sub>LO</sub> = 9.75 GHz
  - (2) f<sub>LO</sub> = 10.60 GHz
  - (3) f<sub>LO</sub> = 11.30 GHz

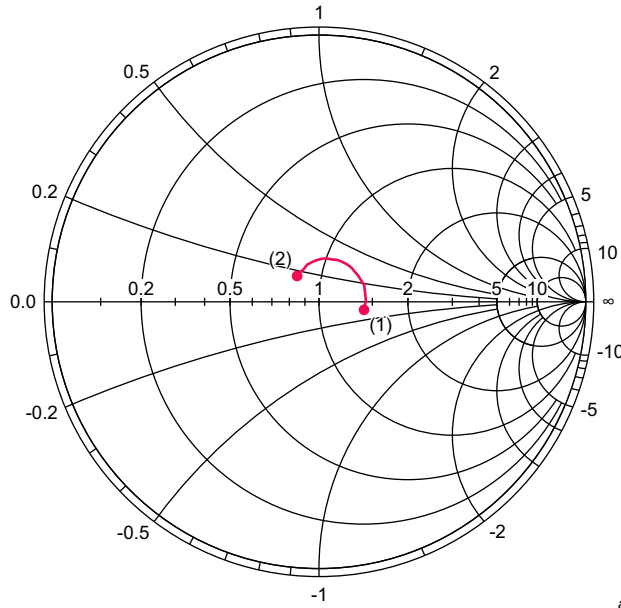
Fig 7. Conversion gain as a function of RF frequency; typical values



- (1) f<sub>RF</sub> = 10.70 GHz
- (2) f<sub>RF</sub> = 12.75 GHz

Fig 8. Input reflection coefficient (S<sub>11</sub>); typical values

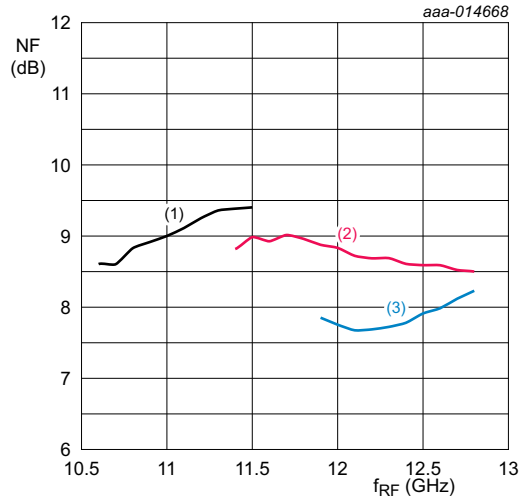




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- (1)  $f_{IF} = 250$  MHz
- (2)  $f_{IF} = 2150$  MHz

**Fig 9. Output reflection coefficient ( $S_{22}$ ); typical values**



- $V_{CC} = 5$  V.
- (1)  $f_{LO} = 9.75$  GHz
  - (2)  $f_{LO} = 10.60$  GHz
  - (3)  $f_{LO} = 11.30$  GHz

**Fig 10. Noise figure as function of RF frequency; typical values**

13. Application information

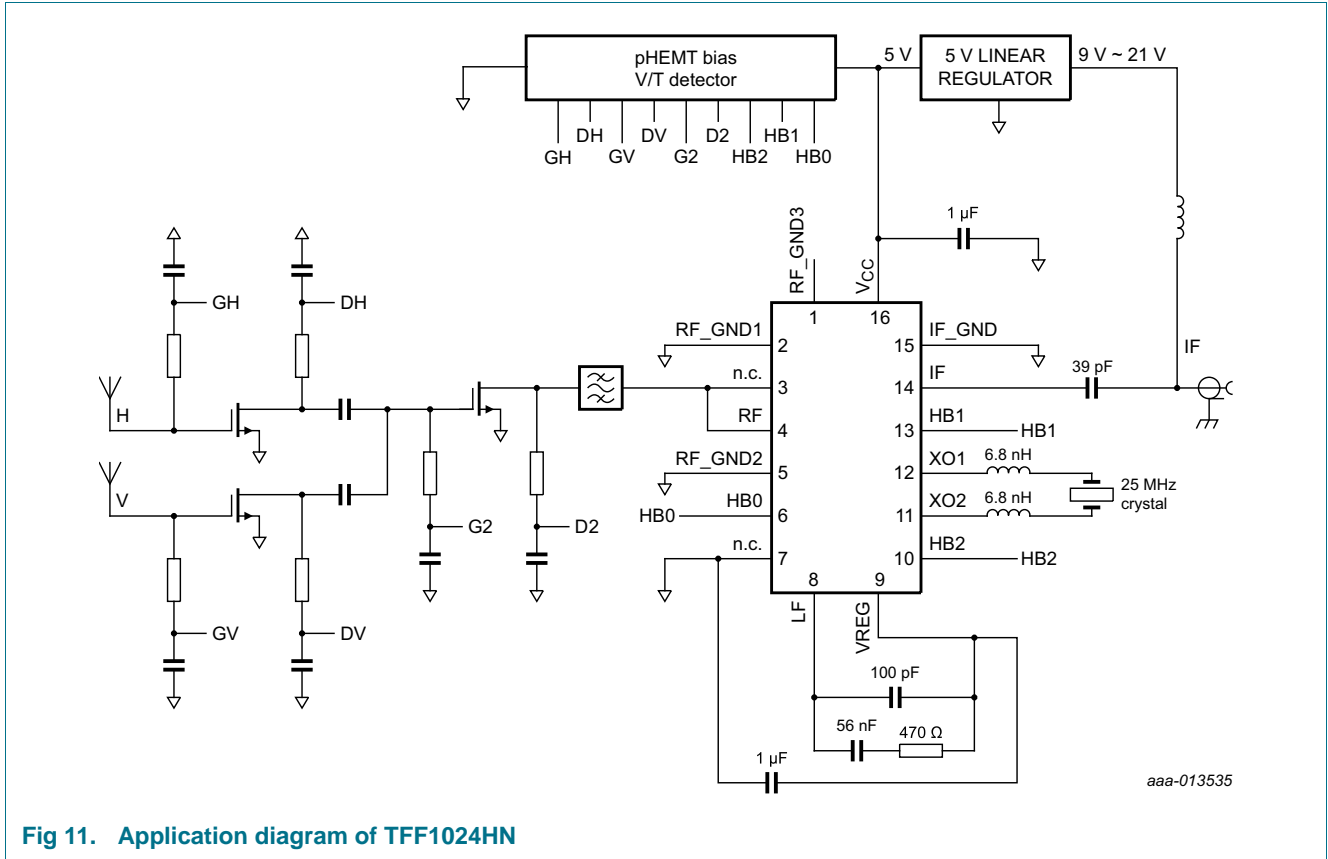


Fig 11. Application diagram of TFF1024HN

Table 9. List of netnames

See [Figure 11](#).

Netname	Description
GH	Gate voltage of 1st stage LNA. Horizontal polarization
DH	Drain voltage of 1st stage LNA. Horizontal polarization
GV	Gate voltage of 1st stage LNA. Vertical polarization
DV	Drain voltage of 1st stage LNA. Vertical polarization
G2	Gate voltage of 2nd stage LNA
D2	Drain voltage of 2nd stage LNA
HB0	LO frequency selection, LSB
HB1	LO frequency selection
HB2	LO frequency selection, MSB

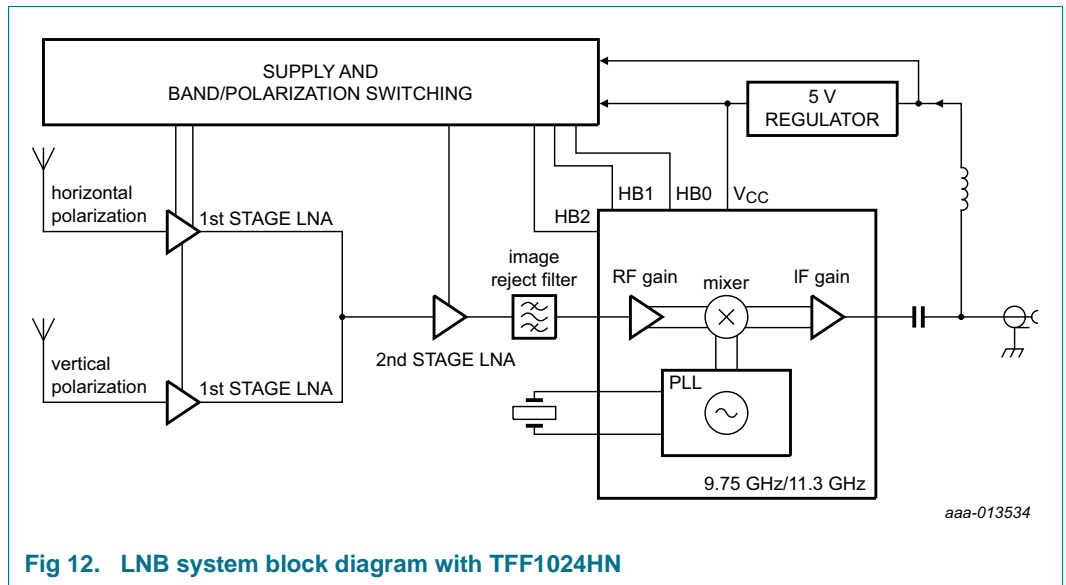


Fig 12. LNB system block diagram with TFF1024HN

14. Package outline

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm

SOT763-1

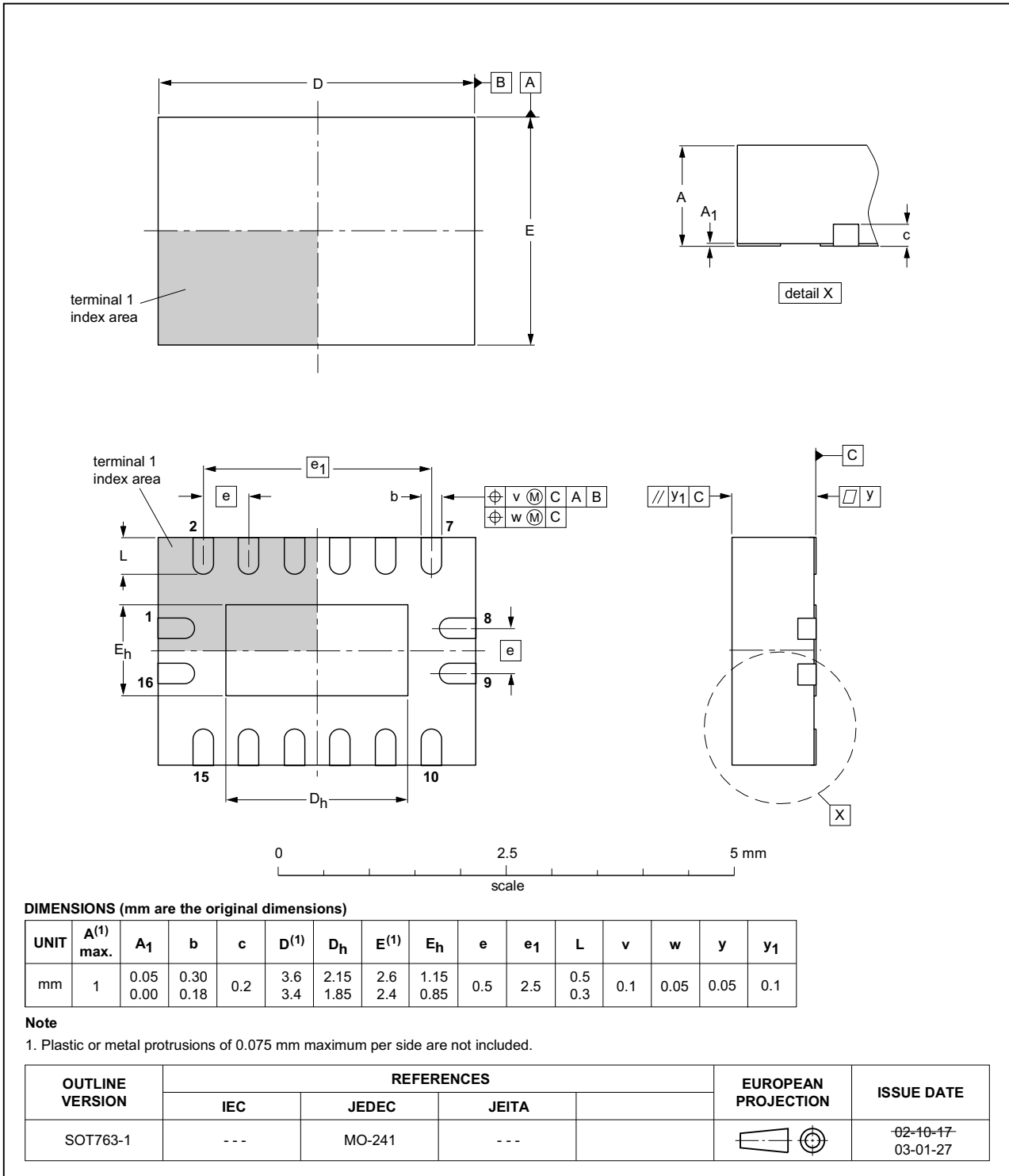


Fig 13. Package outline SOT763-1

## 15. Abbreviations

Table 10. Abbreviations

Acronym	Description
CPW	CoPlanar Waveguide
DVB-S	Digital Video Broadcasting by Satellite
DVB-S2	Digital Video Broadcasting - Satellite - Second generation
ESD	ElectroStatic Discharge
IF	Intermediate Frequency
K <sub>u</sub> band	K-under band
LNA	Low-Noise Amplifier
LNB	Low-Noise Block
LO	Local Oscillator
LSB	Least Significant Bit
MSB	Most Significant Bit
pHEMT	Pseudomorphic High Electron Mobility Transistor
PLL	Phase-Locked Loop
RBW	Resolution BandWidth
VSAT	Very Small Aperture Terminal
V/T	Voltage / Tone
VBW	Video BandWidth

## 16. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
TFF1024HN v.1	20150113	Product data sheet	-	-

## 17. Legal information

### 17.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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